Silicon Strip Sensor Simulations

MSSD capacities – FZ200N and FZ Y-types

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Silicon Strip Sensor Simulations
Phase II Meeting, 03.08.2012

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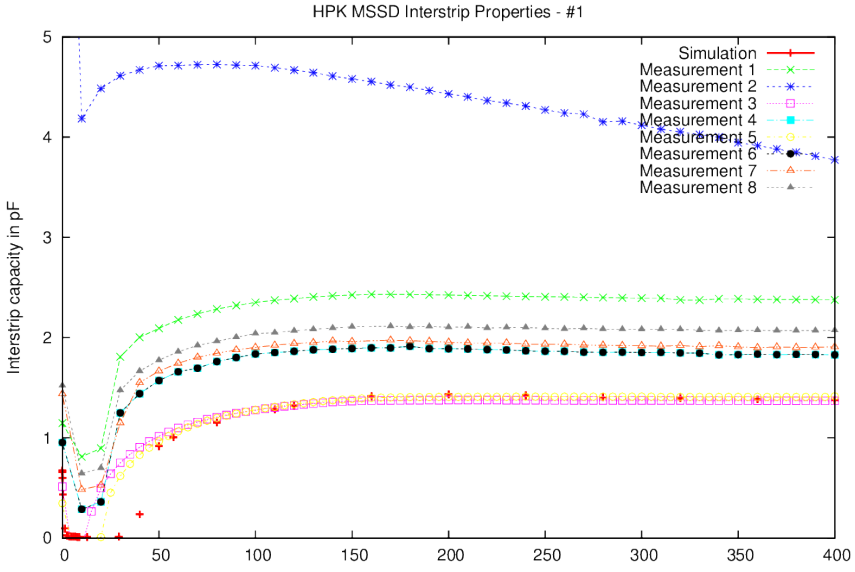
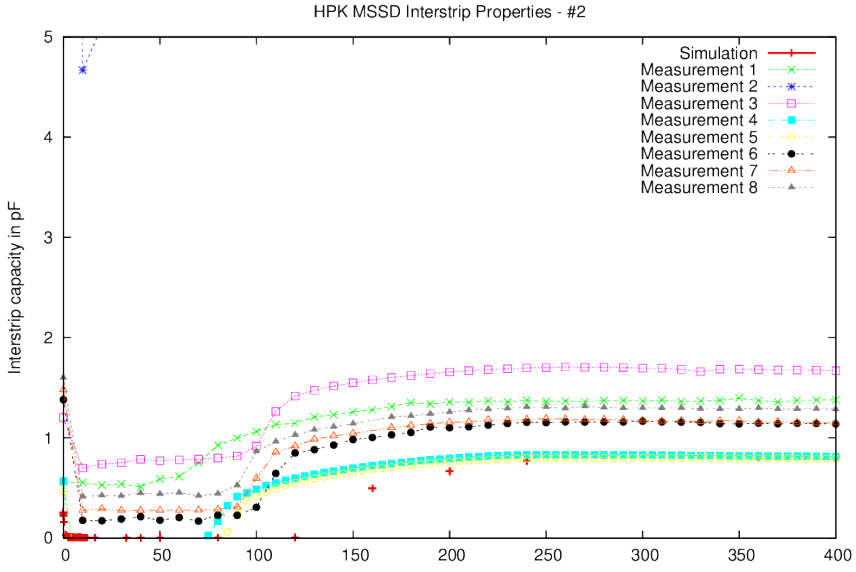
DESY

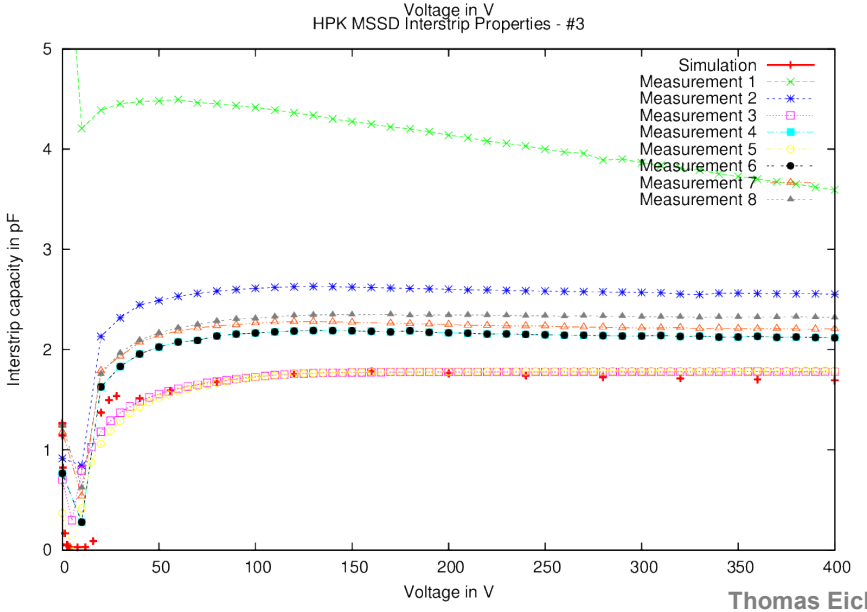
Status / Issues

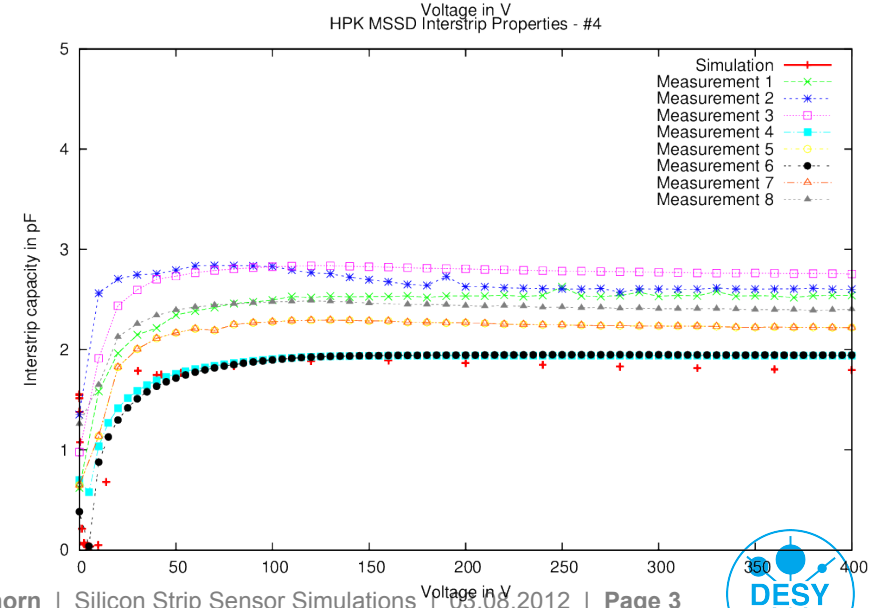
- Comparison of FZ200N C_{int}-curves with measurement shows good agreement
  - Better and easier LyonDB access, but far from optimal
- Still waiting on Uni Delhi data for further Synopsys/Silvaco cross-check
- Data for leakage current shows very large spread – database gives no indication what is correct
- Closer inspection of p-spray data shows some problems – isolation does not prevent electron accumulation → strip short circuit?
  - Strange CV-shape

Results – C_{int} for FZ200N region #1 to #4

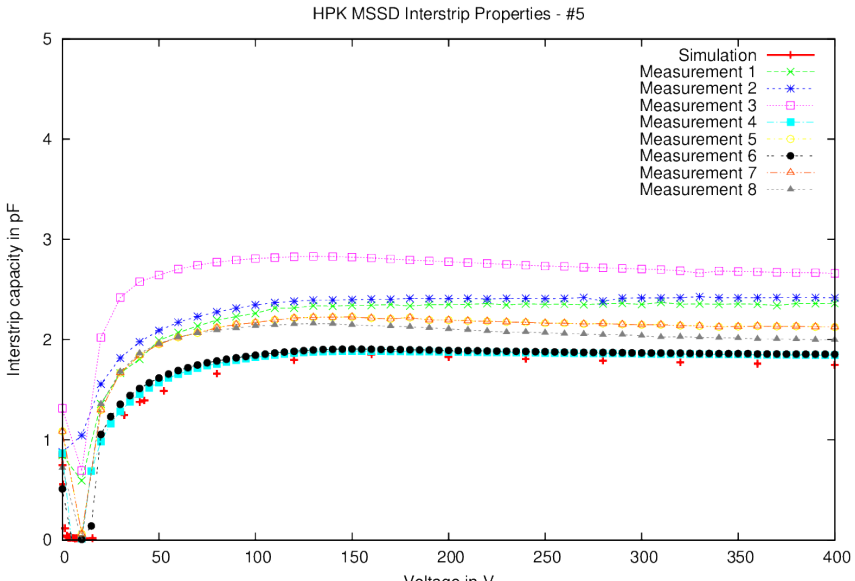


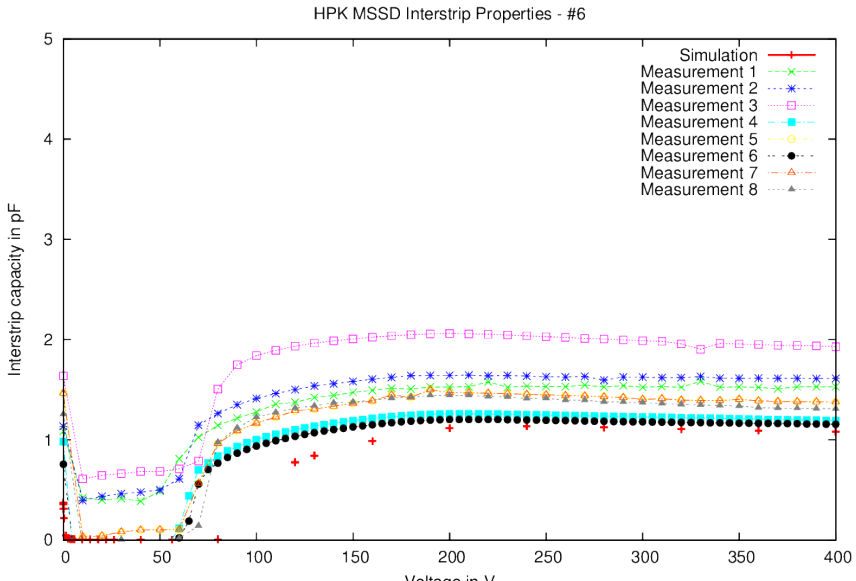


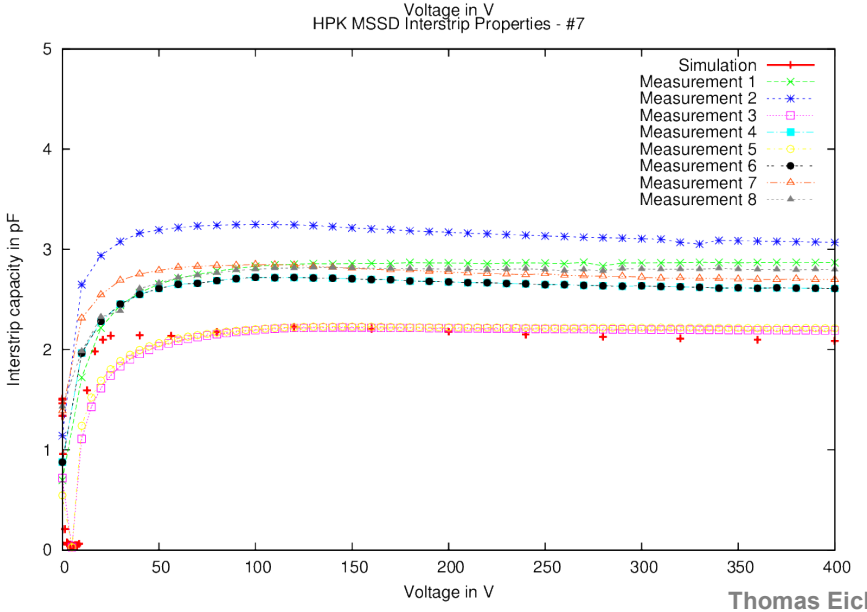


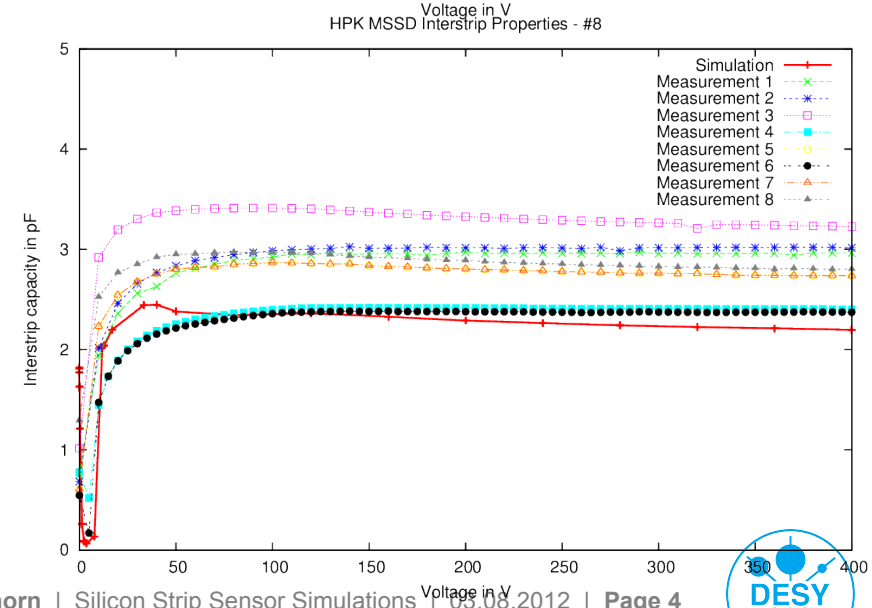


Results – C_{int} for FZ200N region #5 to #8

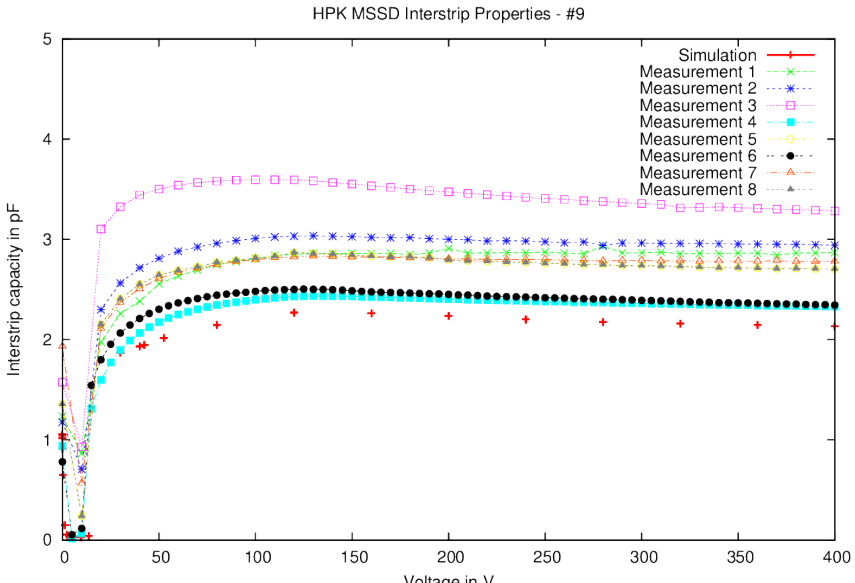


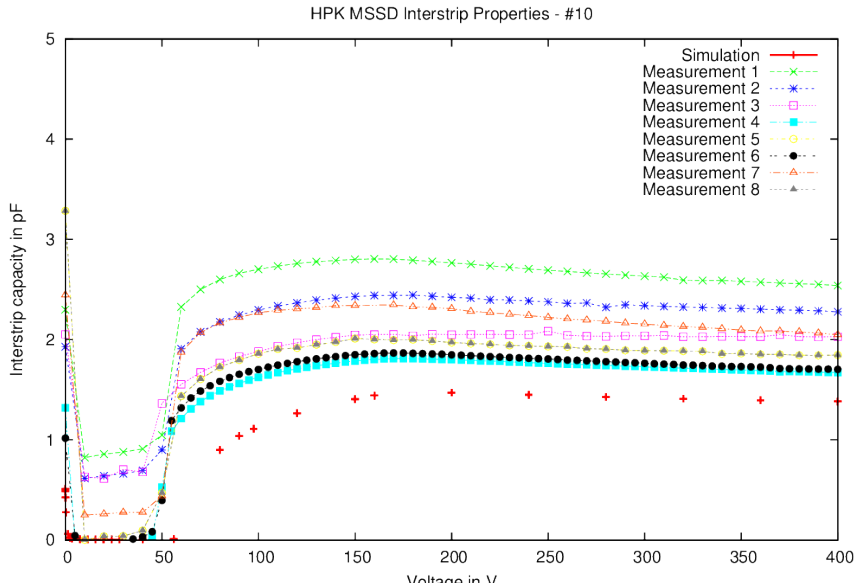


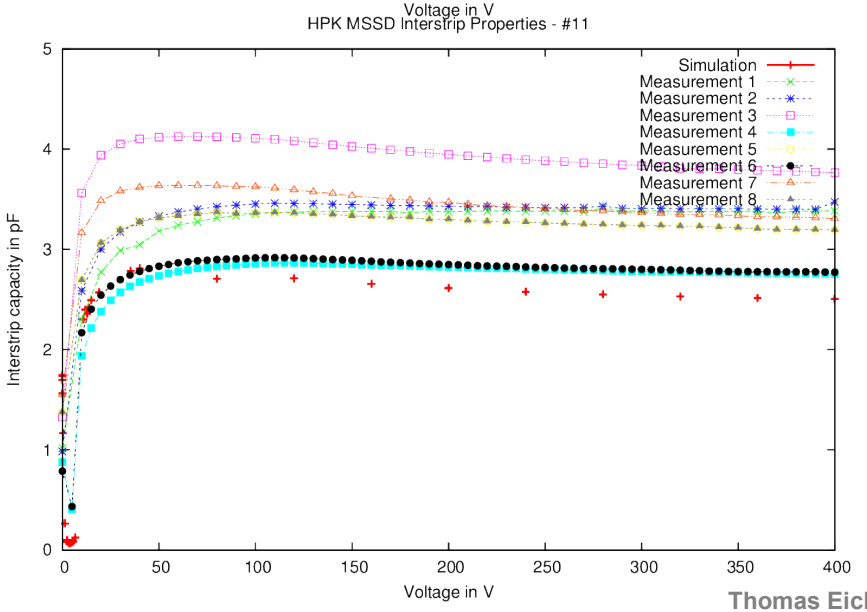


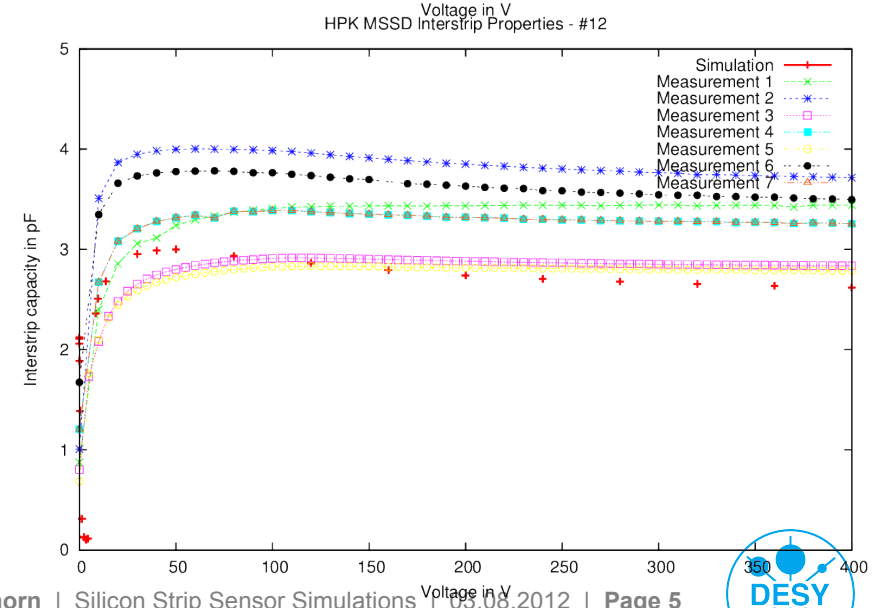


Results – C_{int} for FZ200N region #9 to #12



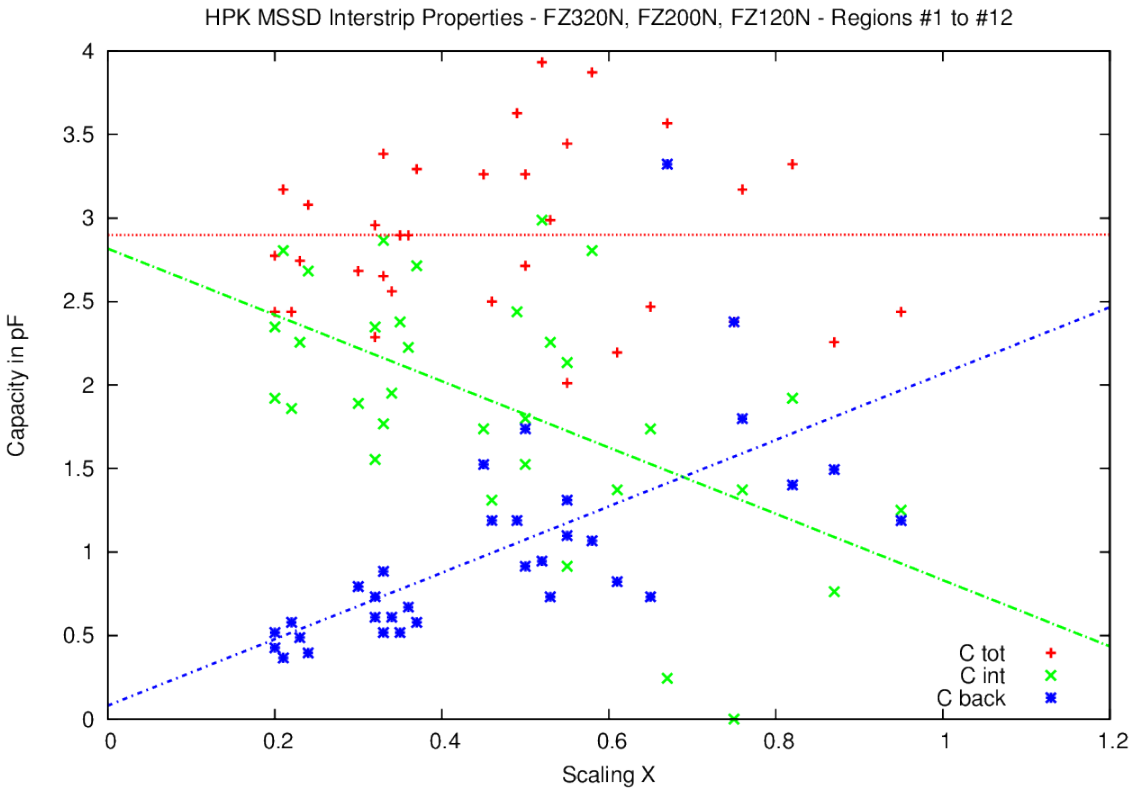






Summary of n-type capacities

- Simulation does not fit as good as for FZ320N
  - Final capacity slightly smaller than lowest measurement
- Detailed curve comparison of FZ120N to come...
- Prediction of $C_{tot} = C_{int} + C_{back}$ can still be confirmed for all n-type sizes and regions

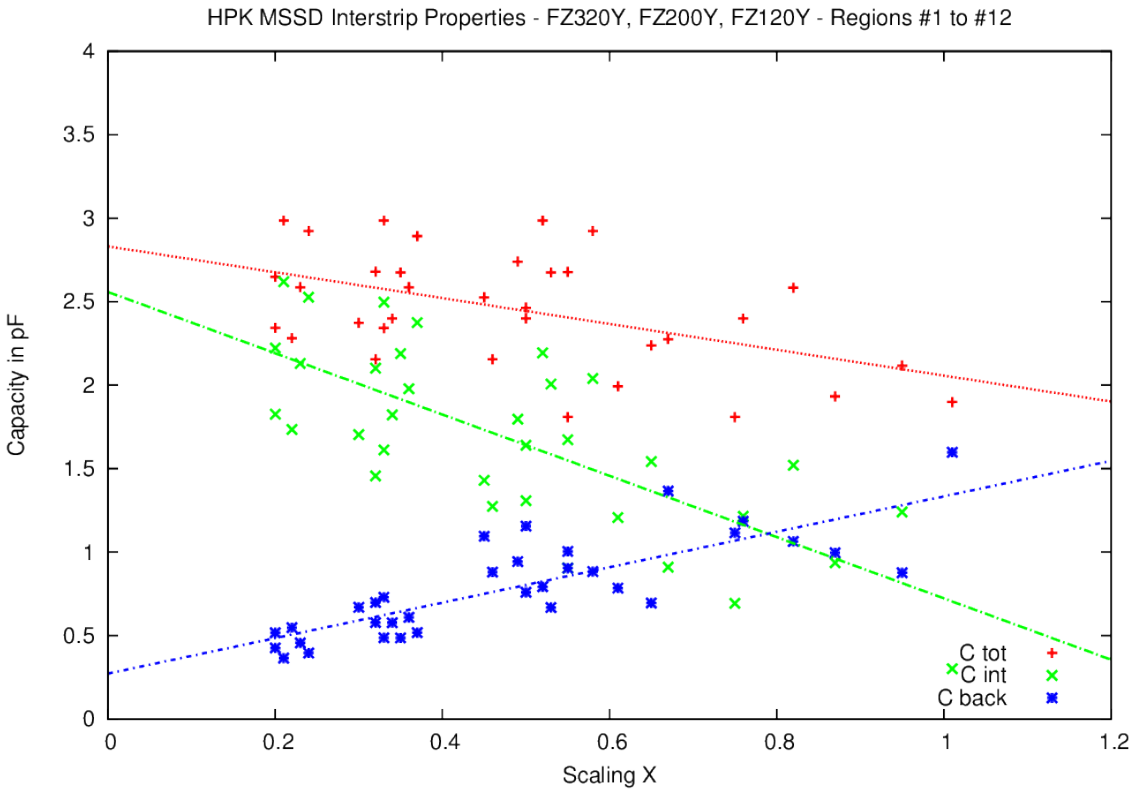


p-spray capacities

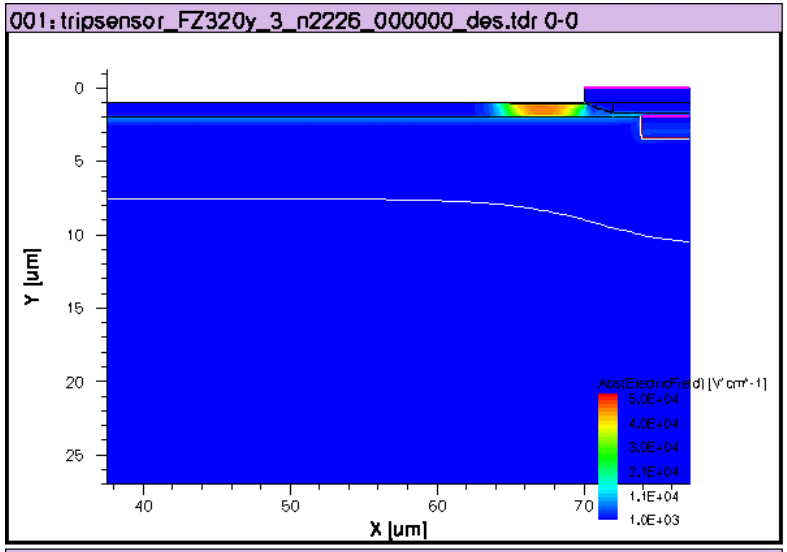
- Some bugs (negative voltage, etc.) in capacitance extraction fixed :-)
  - Not yet perfect for curve extraction

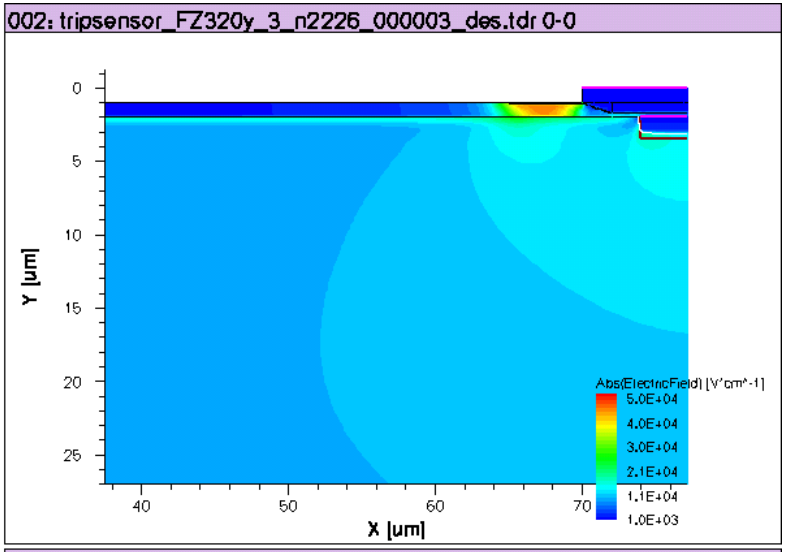
- Spread in capacities smaller, but C_{tot} no longer constant

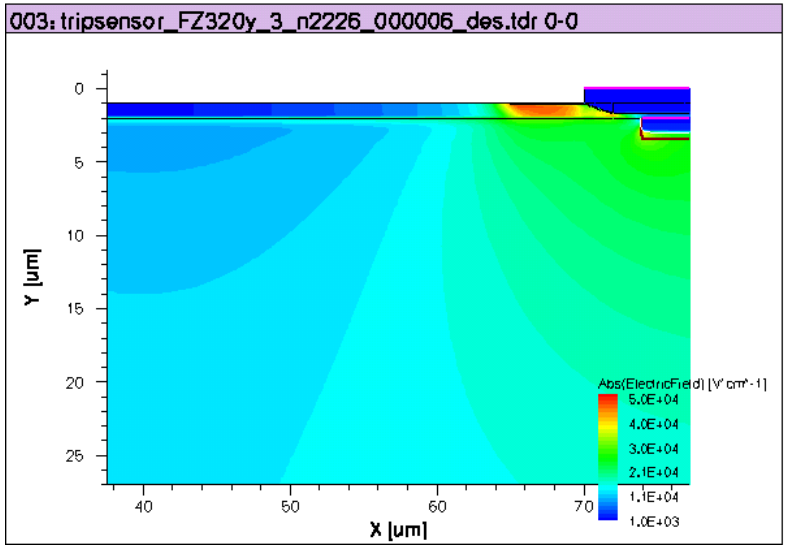
- Does the spray isolation actually work?

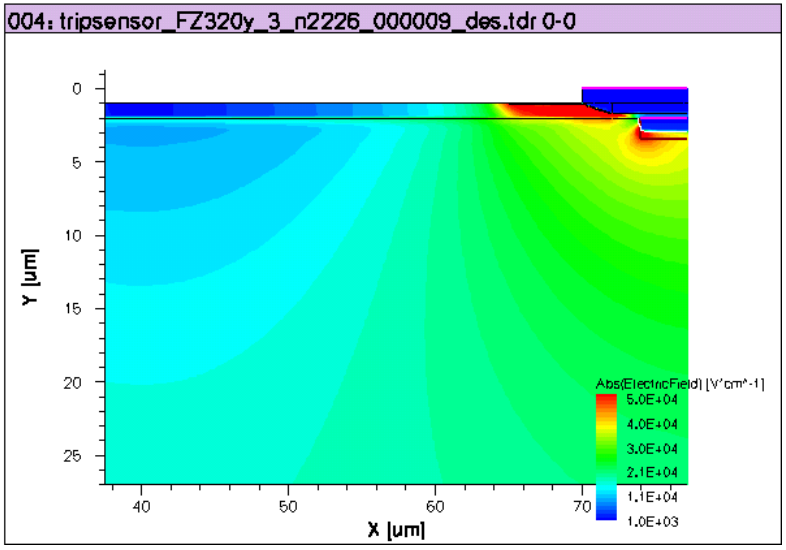


Electric field



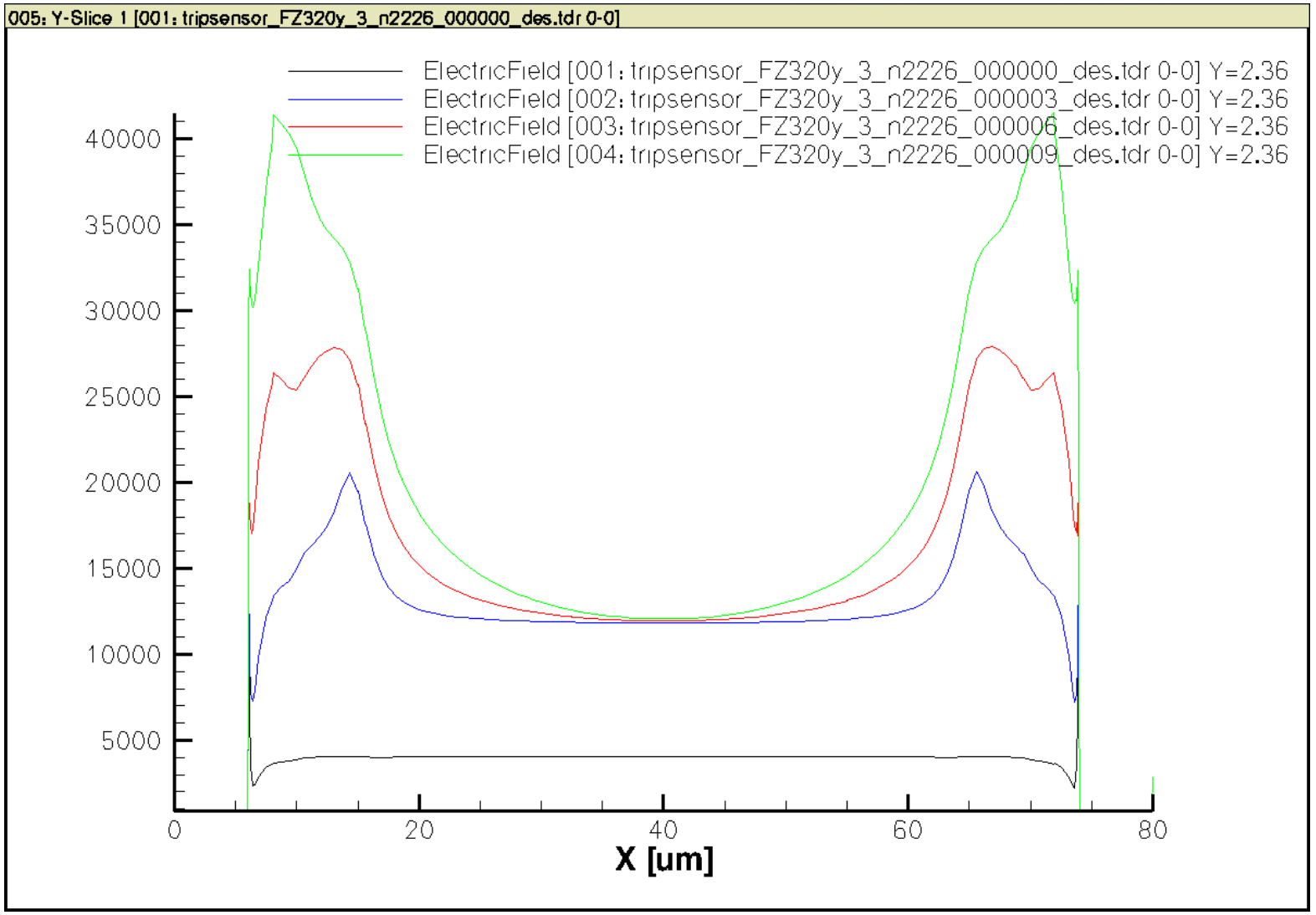






Electric field cut

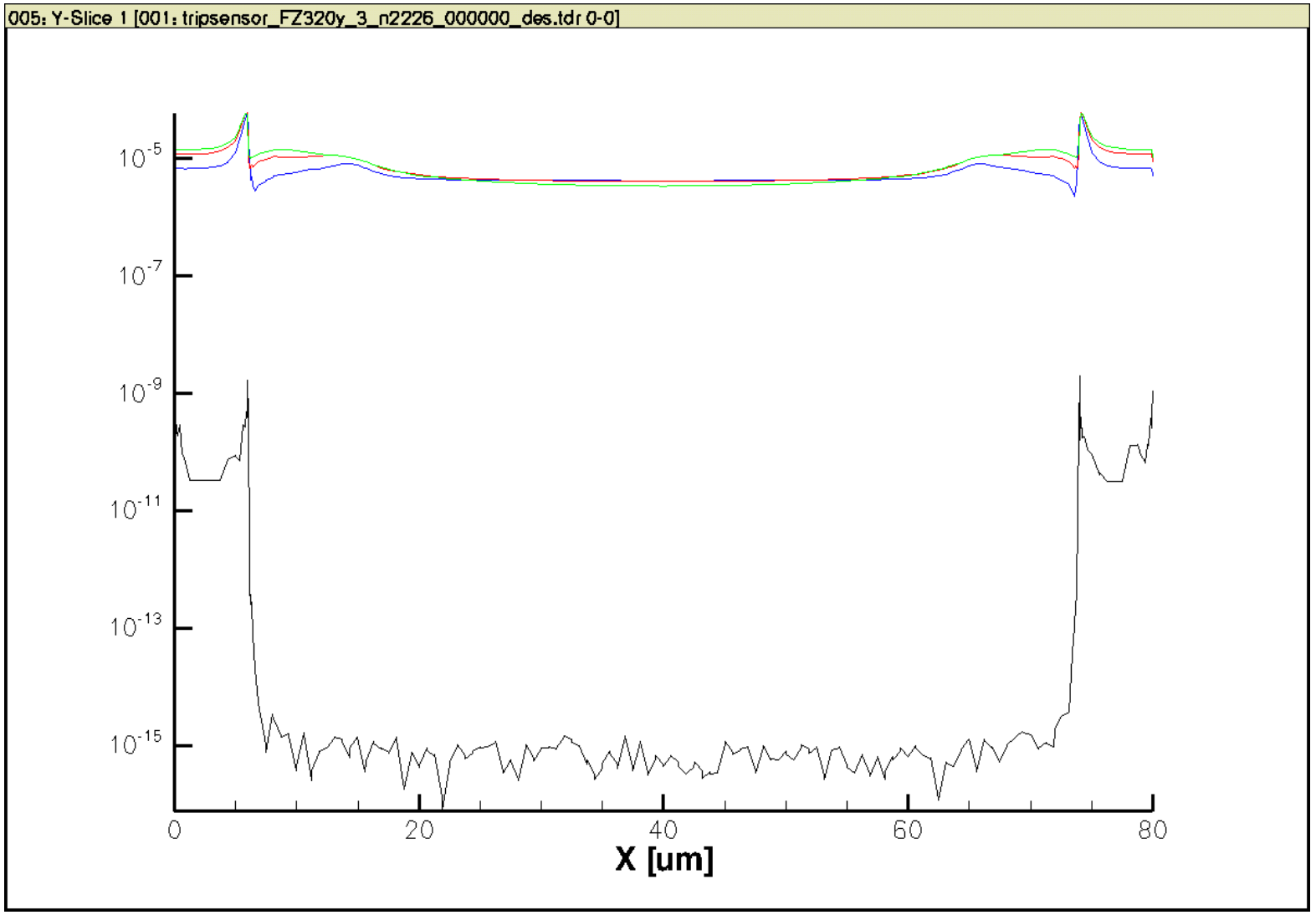
V/cm



Current flow

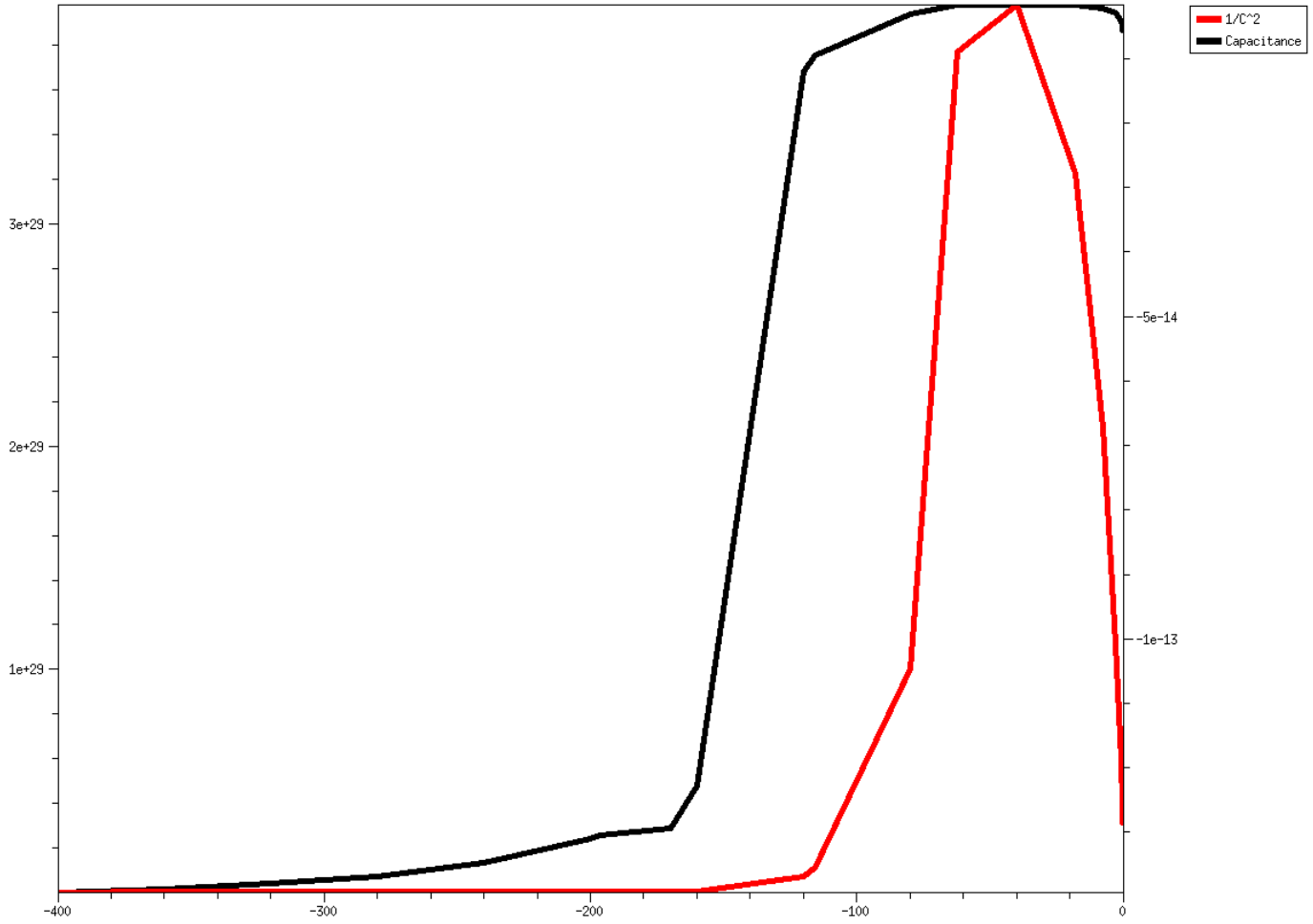
A/cm^2

→ 10e-11 A/µm²



CV behaviour

- Negative capacity?



Backup

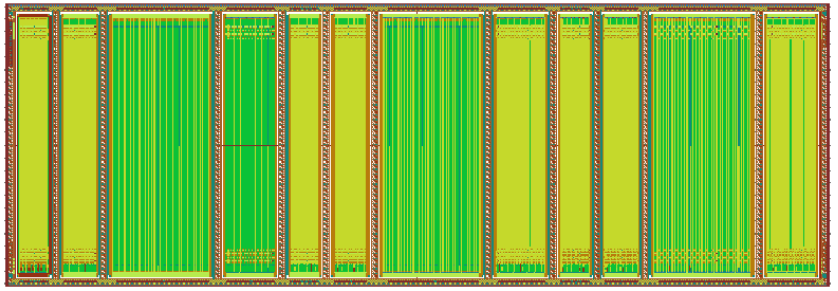
MSSD properties

- 12 strip sensor regions with different pitch and width → interstip capacitance C_{int} should vary
- Scaling factor X for comparison:

$$X = p / [d + p*f(w/p)] \quad \text{with}$$

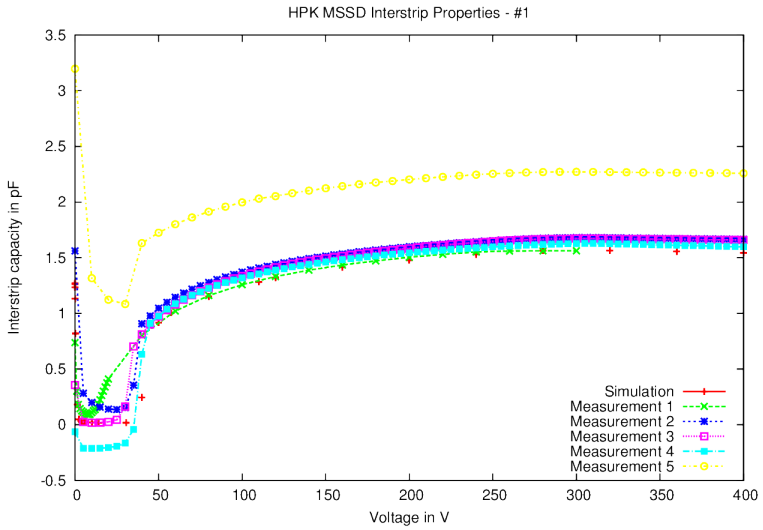
$$f(w/p) = -0{,}00111(w/p)^{-2} + 0{,}0586(w/p)^{-1} + 0{,}24 - 0{,}651(w/p) + 0{,}355(w/p)^2$$

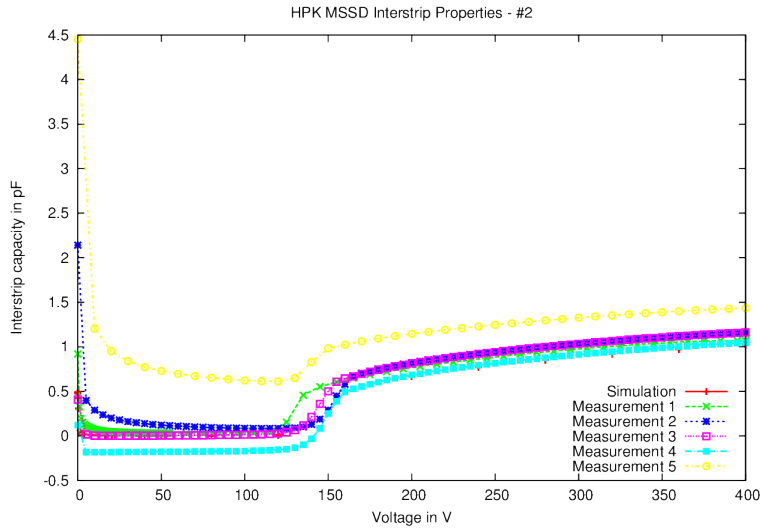
- Measurements: total sensor capacity $C_{tot} = C_{int} + C_{back}$ is constant for all X → try to reproduce in simulations

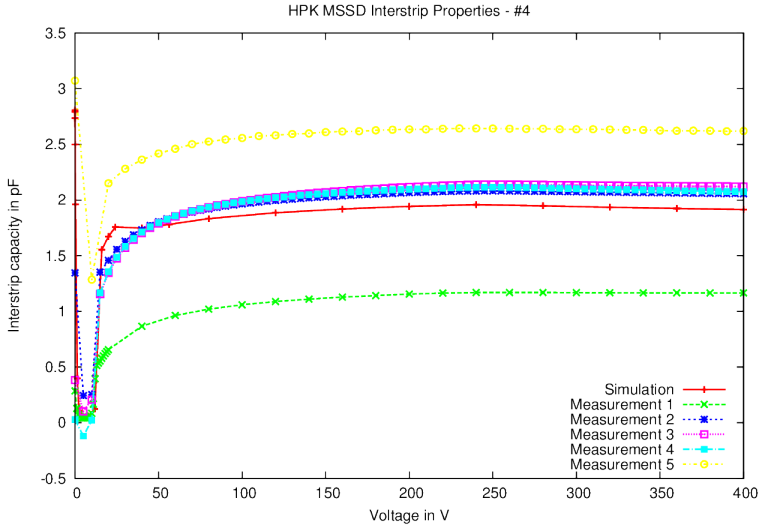


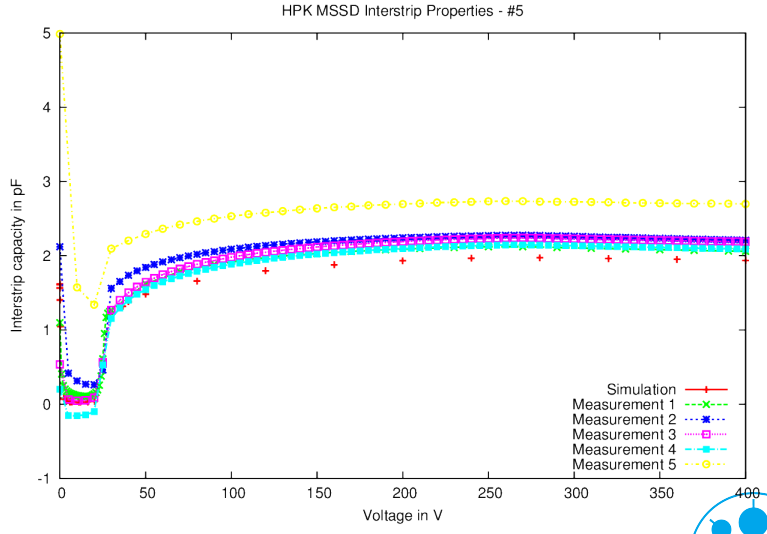
Sensor	Pitch [µm]	Implant width [µm]	Alu width [µm]	w/p	X
1	120	16	29	0,133	0,31
2	240	34	47	0,142	0,54
3	80	10	23	0,125	0,22
4	70	8,5	21,5	0,121	0,19
5	120	28	41	0,233	0,33
6	240	58	71	0,242	0,6
7	80	18	31	0,225	0,23
8	70	15,5	28,5	0,221	0,2
9	120	40	53	0,333	0,35
10	240	82	95	0,342	0,64
11	80	26	39	0,325	0,24
12	70	22,5	35,5	0,321	0,21

Results – C_{int} for FZ320N region #1, #2, #4, #5

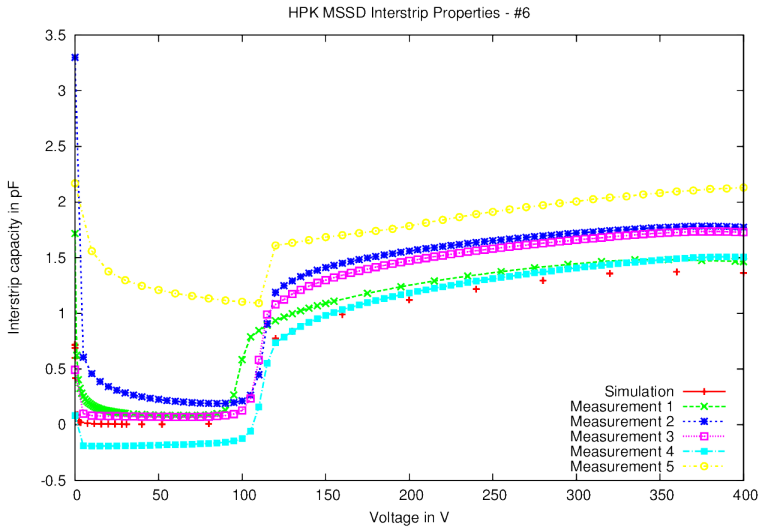


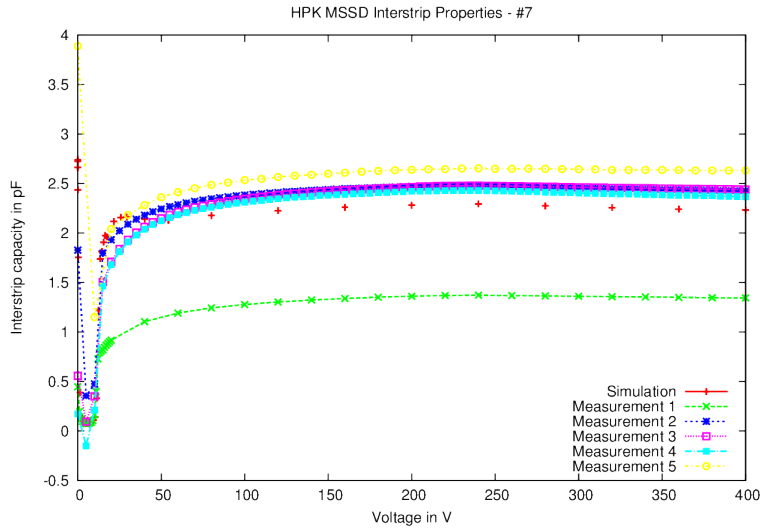


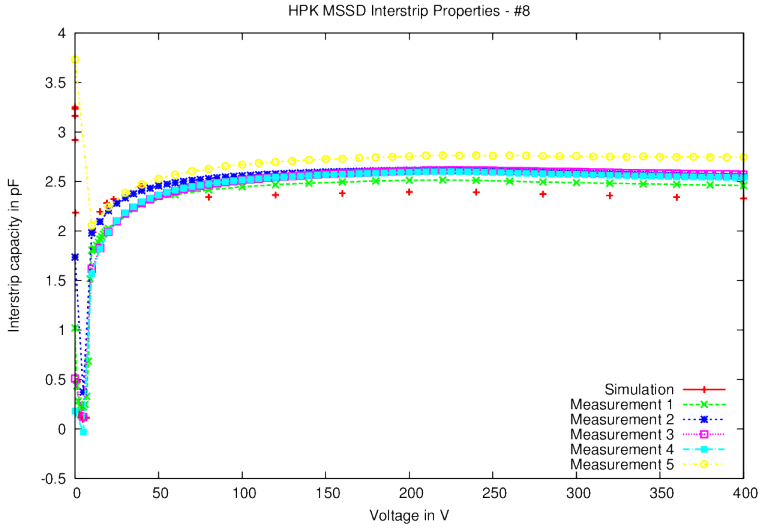


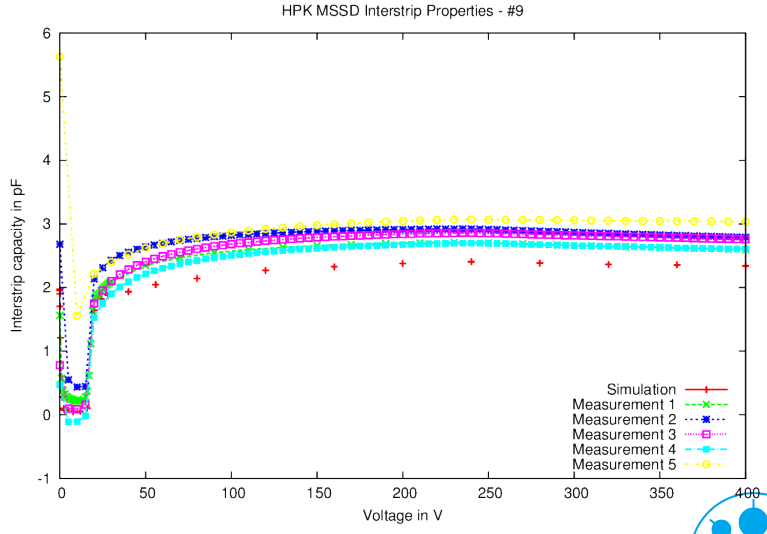


Results – C_{int} for FZ320N region #6 to #9

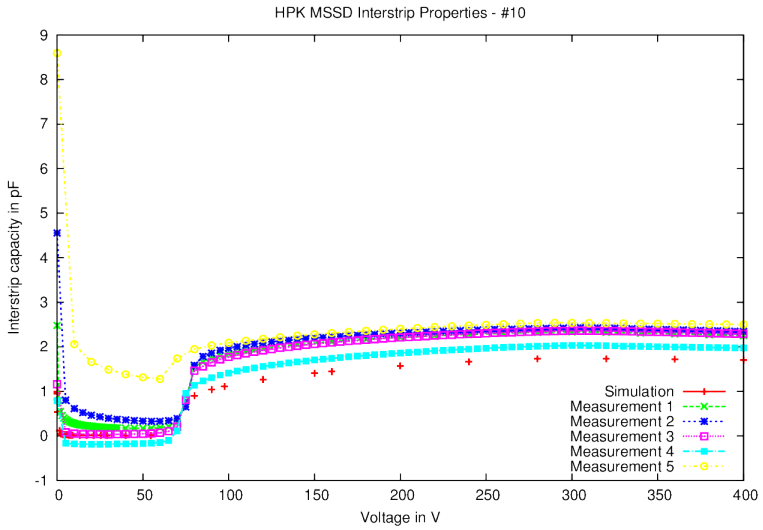


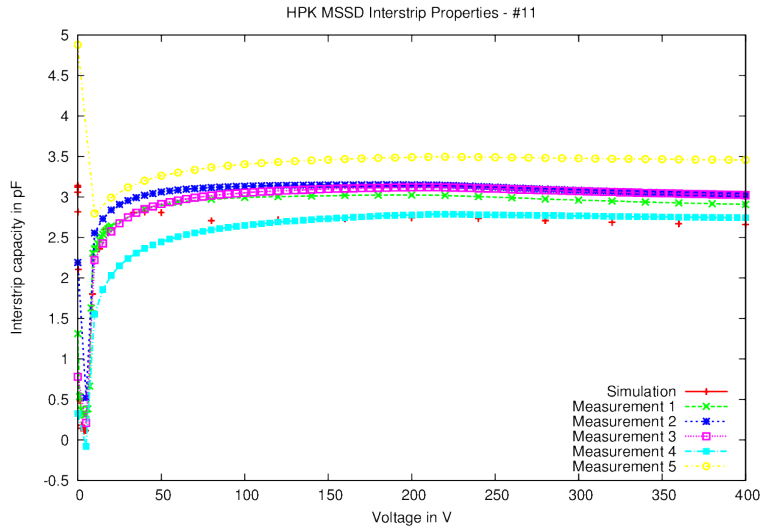


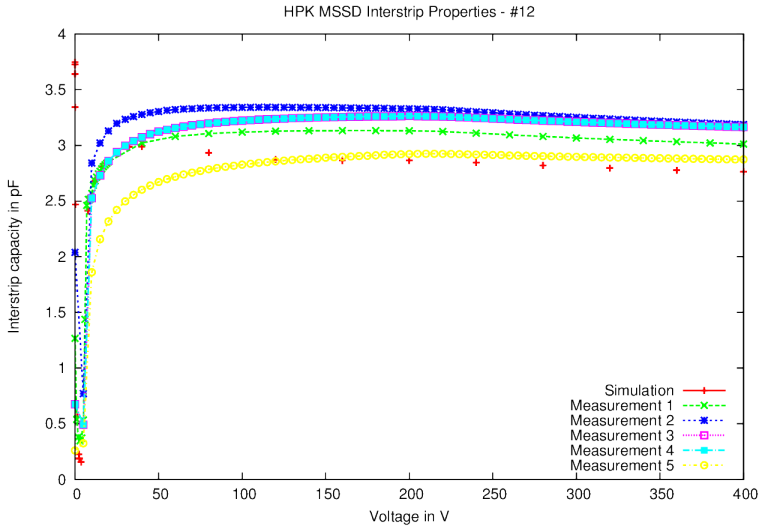




Results – C_{int} for FZ320N region #10, to #12



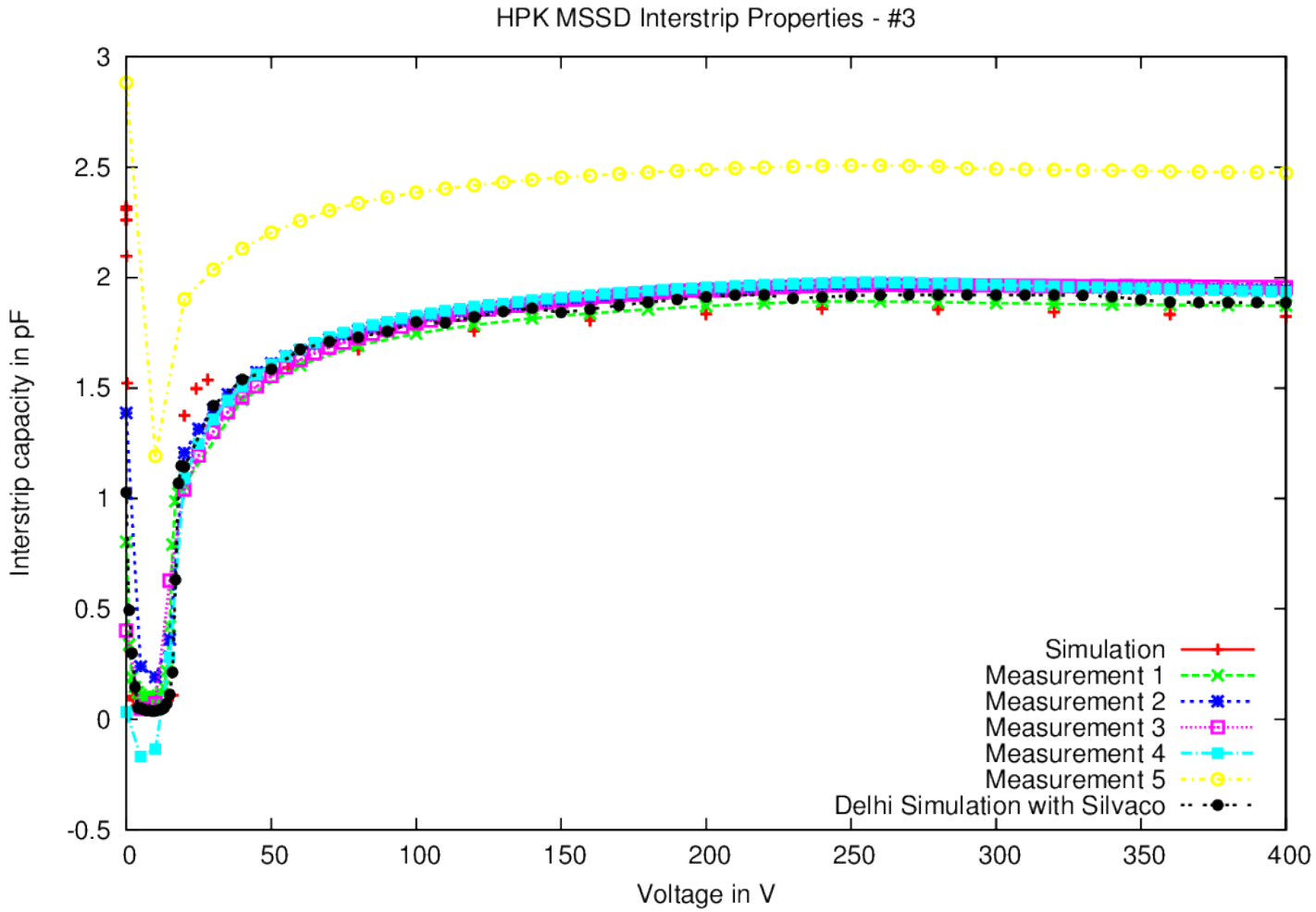




- Quality of results differs between regions
- Curve “shape” is reproduced
- Simulated C_{int} usually lower
- Large improvement achieved

DESY

Results – C_{int} for FZ320N region #3

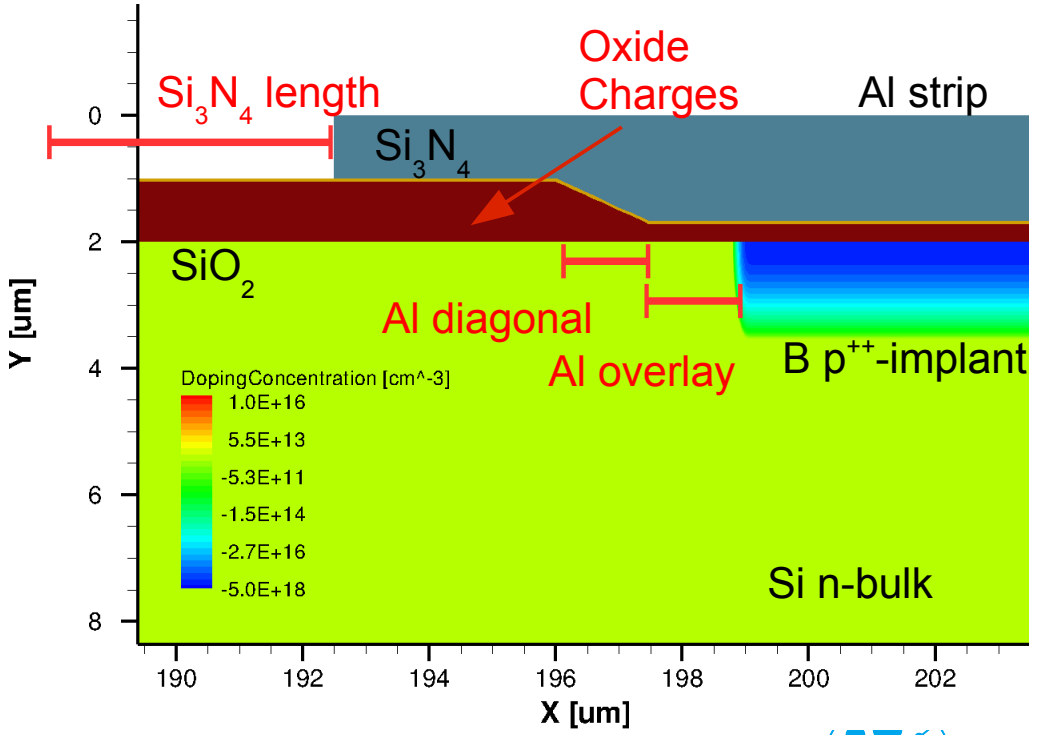


- Synopsys and Silvaco give the same results, in agreement with data!

DESY

Simulation details – parameter settings

- Unchanged: all specified sensor geometries, measurement protocols:
  - Strip width & pitch, sensor thickness, temperature (21°C), AC frequency (1MHz)
- Fixed by previous simulations:
  - Doping concentration (bulk: 3e12cm^{-3}, back/strips: 5e18cm^{-3}), doping profile (strip: gaussian, back: erf)
- Fixed by measurements:
  - Al, SiO_2, Si_3N_4 and implant thicknesses (1µm, 0.68µm, 0.05µm & 1,5µm resp.)
- Adjusted to obtain capacities:
  - Al diagonal & overlay, Si_3N_4 length, SiO_2 charge, SiO_2/Si interface charge, Si_3N_4 charge, Si_3N_4/SiO_2 interface charge



Parameter influence on C_{int}

- Si_3N_4 length (0µm - pitch), Si_3N_4 charge (0 – 1.7e12cm^{-3}), Si_3N_4/SiO_2 interface charge (0 – 1.5e12cm^{-3}):
  - No influence (<1%) seen, could be relevant for P/Y-isolation
  - Simulation does not converge for higher charges
- Al diagonal, Al overlay (0µm – (width-implant)/2):
  - Raises C_{int} up to 10%, “optimal” value depends on strip and implant width, ~ 2µm
- SiO_2 charge (0 – 1.2e12cm^{-3}):
  - Small influence on C_{int}, increases simulation time
- SiO_2/Si interface charge (0 – 1.7e12cm^{-3})
  - Can double C_{int}! 1e11cm^{-3} used for previous plots